



# 91D (NET)  
5-15-03  
Mullish 2800  
501.36931CX1  
Expedited Procedure  
Group No. 2813  
6/17/03  
Easter  
Mullish

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: IWASAKI, et al

Serial No.: 09/985,904

Filed: November 6, 2001

For: SEMICONDUCTOR DEVICE HAVING LAYERED  
INTERCONNECT STRUCTURE WITH A COPPER OR PLATINUM  
CONDUCTING FILM AND A NEIGHBORING FILM (As Amended)

Group Art Unit: 2813

Examiner: Stephen W. Smoot

AMENDMENT AFTER FINAL REJECTION

Do not  
Enter  
J.W.S.  
5-19-03  
Assistant Commissioner for Patents  
Washington, D.C. 20231  
Attn: Box AF

May 12, 2003

Sir:  
In response to the Office Action mailed February 11, 2003, please amend the  
above-identified application as follows:

IN THE CLAIMS:

Please amend the claims presently in the application as follows:

D1 1. (Twice Amended) A semiconductor device having a layered interconnection structure including a copper film overlying a surface of a semiconductor substrate, wherein the layered interconnection structure includes the copper film and a neighboring film located adjacent to the copper film, the neighboring film having, as a primary constituent element thereof, an element selected from a group consisting of